



《风光欣》技术资料

S8050

NPN EPITAXIAL SILICON TRANSISTOR

*Description

Audio Power Amplifier Application

Power Switching Application

High Current Application

*Features

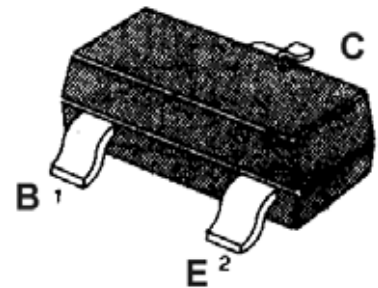
High $h_{FE}=100\sim 320$

Low Collector Saturation Voltage

$V_{CE(sat)}=0.5V(\text{Max.})$ $I_C=500mA, I_B=50mA$

Complementary Pair With S8550

SOT-23



ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EB0}	6	V
Collector Current	I_C	800	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

ELECTRICAL CHARACTERISTICS ($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C=100\mu A, I_E=0$	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=2mA, I_B=0$	25			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E=100\mu A, I_C=0$	6			V
Collector Cut-off Current	I_{CB0}	$V_{CB}=40V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=6V, I_C=0$			100	nA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=800mA$	40	110		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$		0.98	1.2	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=50mA$	100	190		MHz
Collector Output Capacitance	C_{ob}	$f=1MHz, V_{CB}=10V, I_E=0$		9	20	pF